Number 1	stamp	Time	DB	Search Text	Hits	L
1438/\$.ccls. or 257/\$.ccls. USPAT; 2004/11 US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; E	-				nics	
1082 (438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or multiple or multilayer\$2)) ((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or multiple or multilayer\$2)) ((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or multiple or multilayer\$2)) ((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or multiple or multilayer\$2)) and ((etch\$3 or pattern\$3) near5 (metal or conductor or multilayer\$2)) and ((etch\$3 or pattern\$3) near5 (metal or conductor or multiple or multilayer\$2)) and ((etch\$3 or pattern\$3) near5 (metal or conductor or multiple			USPAT	("6143476").PN.	1	1
1082			US-PGPUB;	438/\$.ccls. or 257/\$.ccls.	359125	-
multilayer\$2)			IBM_TDB USPAT;		1082	_
adj mask\$3) same (third or multiple or multiple or multiple or pattern\$3) near5 (metal or conductor or wir\$3)) and ((etch\$3 or pattern\$3) same (third or multiple or multilayer\$2))) and ((lotch\$3 or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3 EPO; JPO; JPO; DERWENT; IBM_TDB USPAT; USPEPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	· <i>I</i>	21:37	EPO; JPO; DERWENT;			
Wir\$3)			US-PGPUB; EPO; JPO;	adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 or	635	-
<pre>wir\$3)) and interconnect\$3 ((((438/\$.ccls. or 257/\$.ccls.) and</pre>			IBM_TDB USPAT; US-PGPUB;	<pre>wir\$3)) (((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 or</pre>	401	-
or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric)) (((((438/\$.ccls. or 257/\$.ccls.) and (hlanket near5 (insulat\$3))) and ((etch\$3) or pattern\$3)) and (metal or conductor or wir\$3))) and interconnect\$3) and (metal or conductor or wir\$3))) and interconnect\$3) and (metal or conductor or wir\$3))) and ((tungsten or W)) same (metal or conductor or wir\$3)) and ((tungsten or W)) same (metal or conductor or wir\$3)) and ((tungsten or W)) same (metal or conductor or wir\$3))) and interconnect\$3) and (metal or conductor or wir\$3))) and (metal or conductor or wir\$3))) and (metal or conductor or wir\$3))) and (metal or conductor or wir\$3)) and interconnect\$3) and (metal or conductor or wir\$3))) and interconn			IBM_TDB USPAT; US-PGPUB;	wir\$3))) and interconnect\$3 ((((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or	42	-
<pre>((hard adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric))) and ((tungsten or W) same (bitline or (bit adj2 line))) (((((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric))) and (bitline or (bit adj2 line)) 40 ((((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or</pre>	/11 /05	2004/	DERWENT; IBM_TDB	or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric))	2	
14 (((((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 or pattern\$3)) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric)) and (bitline or (bit adj2 line)) 40 ((((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 or pattern\$3) near5 (metal or conductor or pattern\$3) near5 (metal or conductor or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and IBM_TDB			US-PGPUB; EPO; JPO; DERWENT;	<pre>((hard adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric))) and ((tungsten or W) same</pre>		
- 40 (((((438/\$.ccls. or 257/\$.ccls.) and (USPAT; 2004/11 ((hard adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 EPO; JPO; or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and IBM_TDB			US-PGPUB; EPO; JPO; DERWENT;	<pre>(((((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric))) and (bitline or (bit adj2</pre>	14	_
dielectric))) not (((((438/\$.ccls. or 257/\$.ccls.) and ((hard adj mask\$3) same		1	US-PGPUB; EPO; JPO; DERWENT;	<pre>((hard adj mask\$3) same (third or multiple or multilayer\$2))) and ((etch\$3 or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric))) not (((((438/\$.ccls. or</pre>	40	-
(third or multiple or multilayer\$2))) and ((etch\$3 or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric))) and ((tungsten or W) same (bitline or (bit adj2 line))))				(third or multiple or multilayer\$2))) and ((etch\$3 or pattern\$3) near5 (metal or conductor or wir\$3))) and interconnect\$3) and (blanket near5 (insulat\$3 or dielectric))) and ((tungsten or W) same		